

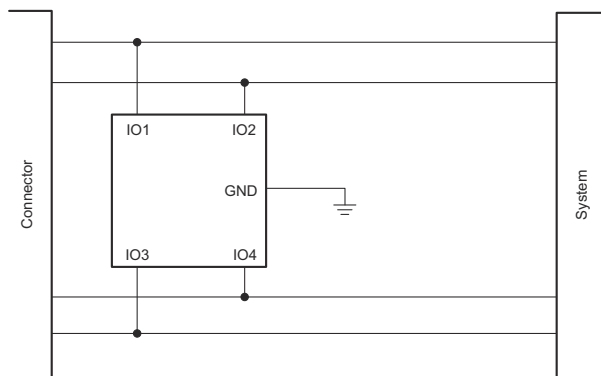
# TPD4E1B06 4 チャンネル超低リーク ESD 保護ダイオード デバイス

## 1 特長

- 超低リーク電流: 0.5nA (最大値)
- 4 本の I/O ラインの過渡保護:
  - IEC 61000-4-2 接触放電  $\pm 12\text{kV}$
  - IEC 61000-4-2 エアギャップ放電  $\pm 15\text{kV}$
  - IEC 61000-4-5 サージ 3.0A (8/20 $\mu\text{s}$ )
- I/O 容量: 0.7pF (標準値)
- 双方向 ESD 保護ダイオード・アレイ
- 低 ESD クランプ電圧
- 産業用温度範囲:  $-40^{\circ}\text{C} \sim 125^{\circ}\text{C}$
- 小型で配線が容易な DRL および DCK パッケージ

## 2 アプリケーション

- 血糖値測定器
- タブレット
- GPS
- 携帯用メディア・プレーヤ
- テレビ
- セット・トップ・ボックス



概略回路図

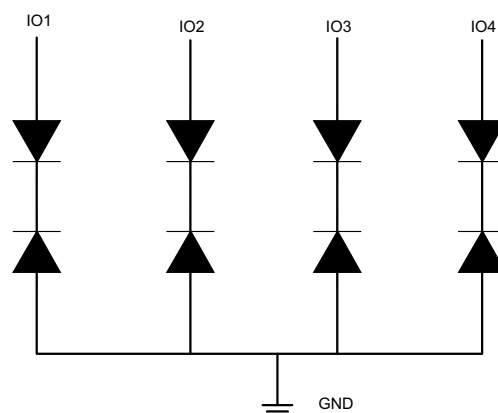
## 3 概要

TPD4E1B06 は、4 チャンネルの双方向静電気放電 (ESD) 保護ダイオード・アレイです。このデバイスは超低リーク電流 (0.5nA) を特長とし、高精度アナログ測定に適しています。 $\pm 12\text{kV}$  接触および  $\pm 15\text{kV}$  エアギャップに対する ESD 保護は、IEC 61000-4-2 レベル 4 要件を上回っています。TPD4E1B06 デバイスのライン容量は 0.7pF で、高精度アナログ、USB 2.0、イーサネット、SATA、LVDS、および 1394 の各インターフェイスに適しています。

### パッケージ情報

部品番号	パッケージ <sup>(1)</sup>	パッケージ・サイズ <sup>(2)</sup>
TPD4E1B06	DCK (SC70, 6)	2mm × 2.1mm
	DRL (SOT, 6)	1.6mm × 1.6mm

- 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
- パッケージ・サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。



機能ブロック図



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## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision C (July 2014) to Revision D (October 2023)	Page
ドキュメント全体にわたって表、図、相互参照の採番方法を更新.....	1
パッケージ・リード・サイズを含めるよう「パッケージ情報」表を更新 .....	1
Updated the <i>Feature Description</i> section.....	8
Updated the <i>Bi-directional (ESD) Protection Diode Array</i> section.....	8

Changes from Revision B (May 2014) to Revision C (July 2014)	Page
Changed 2 device names from TPD4E6B06 to TPD4E1B06 .....	9

Changes from Revision A (January 2013) to Revision B (May 2014)	Page
データシートに DRL パッケージを追加.....	1
Changed $I_{PP}$ , peak pulse current from 3.5 A to 3.0 A.....	4
Added the ESD Ratings table.....	4
Added Recommended Operating Conditions table.....	4
Changed Electrical Characteristics table to reflect operating conditions at 25 °C.....	5
Added MIN $V_{RWM}$ value of –5.5 V.....	5
Changed $V_{CLAMP}$ at $I_{PP} = 1$ A from 10.5 V to 10.9 V. ....	5
Changed Line Capacitance TYP value from 1 pF to 0.7 pF.....	5
Added Line Capacitance MAX value of 0.95 pF. ....	5
Changed $I_{LEAK}$ from MAX of 10 nA to 0.5 nA .....	5

Changes from Revision * (December 2012) to Revision A (January 2013)	Page
Fixed "f" units typo from GHz to MHz for $C_L$ parameter in ELECTRICAL CHARACTERISTICS table.....	5

## 5 Pin Configuration and Functions

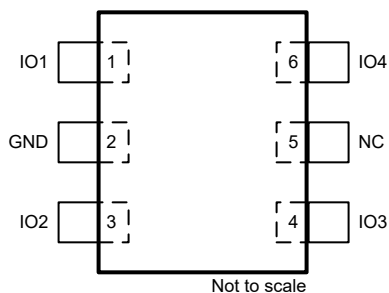


図 5-1. DCK Package, 6-Pin SC70 (Top View)

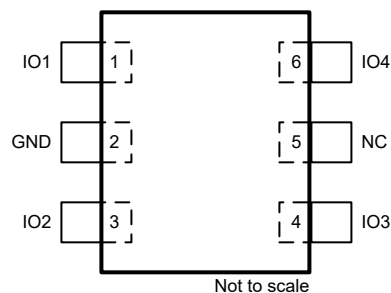


図 5-2. DRL Package, 6-Pin SOT (Top View)

表 5-1. Pin Functions

PIN			TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.			
	DCK	DRL		
IO1	1	1	I/O	ESD protected channel. Connect to data line as close to the connector as possible.
IO2	2	3	I/O	ESD protected channel. Connect to data line as close to the connector as possible.
IO3	4	4	I/O	ESD protected channel. Connect to data line as close to the connector as possible.
IO4	5	6	I/O	ESD protected channel. Connect to data line as close to the connector as possible.
GND	3	2	GND	Ground
NC	6	5	NC	Not internally connected

(1) I = input, O = output, GND = ground, NC = no connection

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

	MIN	MAX	UNIT
Operating temperature range	–40	125	°C
$I_{PP}$ , peak pulse current ( $t_p = 8/20 \mu s$ ), IO pin to GND		3.0	A
$P_{PP}$ , peak pulse power ( $t_p = 8/20 \mu s$ )		45	W

- (1) Operation outside the *Absolute Maximum Rating* may cause permanent device damage. *Absolute Maximum Rating* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Condition*. If used outside the *Recommended Operating Condition* but within the *Absolute Maximum Rating*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

### 6.2 ESD Ratings

			MIN	MAX	UNIT
T <sub>stg</sub>	Storage temperature range		−65	155	°C
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	−4.0	4.0	kV
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	−1.5	1.5	
		IEC 61000-4-2 contact ESD	−12	12	
		IEC 61000-4-2 air-gap ESD	−15	15	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Pins listed as 4 kV may actually have higher performance.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Pins listed as 1.5 kV may actually have higher performance.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
$V_{IO}$ The voltage between any two device pins should not exceed 5.5 V	–5.5	5.5	V
$T_A$ Operating free-air temperature	–40	125	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPD4E1B06		UNIT
		DCK	DRL	
		6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	227.3	233.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	79.5	95.5	
$R_{\theta JB}$	Junction-to-board thermal resistance	72.1	68.1	
$\Psi_{JT}$	Junction-to-top characterization parameter	3.6	7.6	
$\Psi_{JB}$	Junction-to-board characterization parameter	70.4	67.9	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{RWM}$	Reverse stand-off voltage		-5.5		5.5	V
$V_{CLAMP}$	Clamp voltage with ESD strike, IO to GND	$I_{PP} = 1\text{ A}$ , $t_p = 8/20\text{ }\mu\text{Sec}$ , from I/O to GND or GND to I/O		10.9		V
		$I_{PP} = 3\text{ A}$ , $t_p = 8/20\text{ }\mu\text{Sec}$ , from I/O to GND or GND to I/O		14.5		V
$R_{DYN}$	Dynamic resistance	$I_{TLP} = 10\text{ A to }20\text{ A}$ , I/O to GND		1		$\Omega$
		$I_{TLP} = 10\text{ A to }20\text{ A}$ , GND to I/O		0.8		
$C_L$	Line capacitance	$f = 1\text{ MHz}$ , $V_{BIAS} = 2.5\text{ V}$		0.7	0.95	pF
$V_{BR}$	Break-down voltage	$I_{IO} = 1\text{ mA}$ , from I/O to GND or GND to I/O	7		9.5	V
$I_{LEAK}$	Leakage current	$V_{IO} = 2.5\text{ V}$			0.5	nA

## 6.6 Typical Characteristics

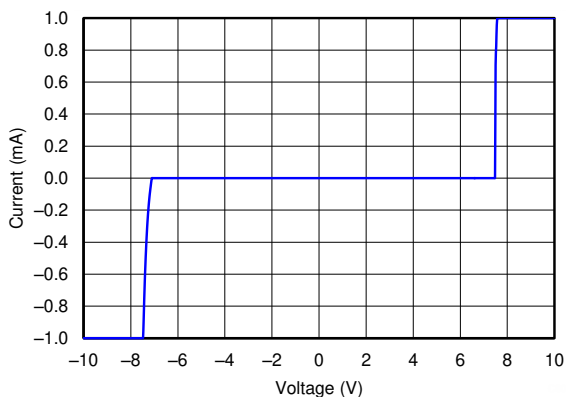


図 6-1. DC Voltage Sweep I-V Curve

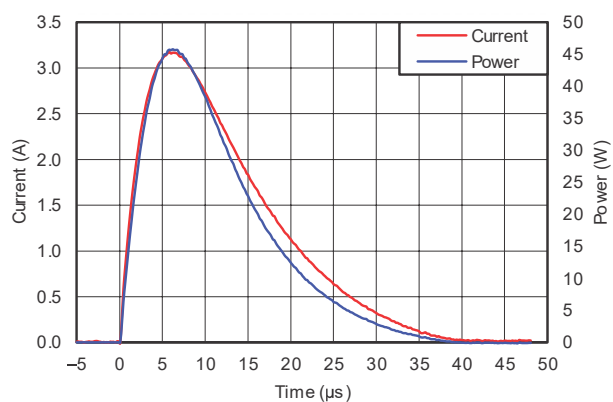


図 6-2. Surge Curve ( $t_p = 8/20 \mu s$ ), Pin IO to GND

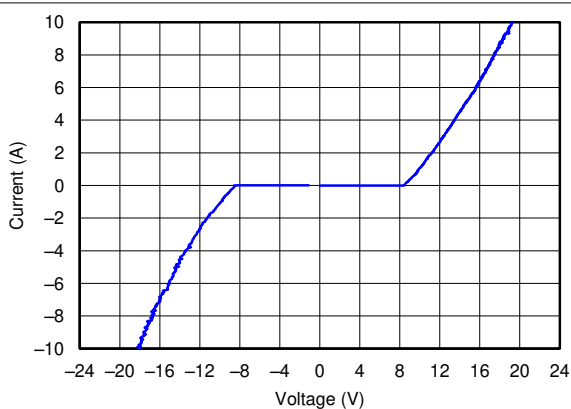


図 6-3. TLP Plot IO to GND

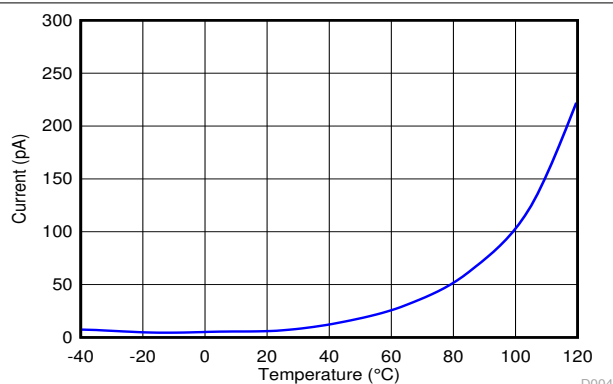


図 6-4. Leakage vs Temperature

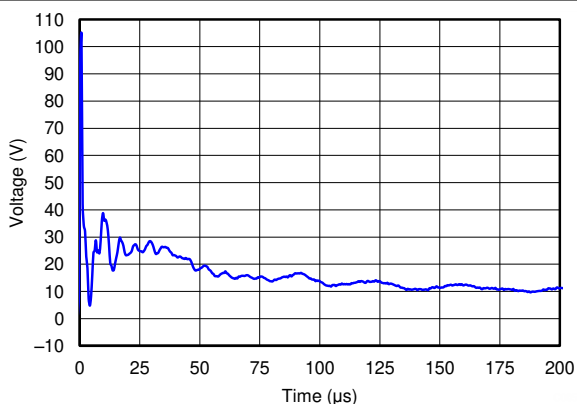


図 6-5. +8 kV IEC Waveform

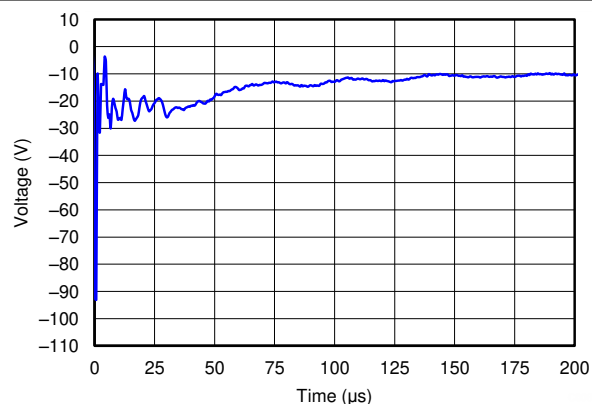
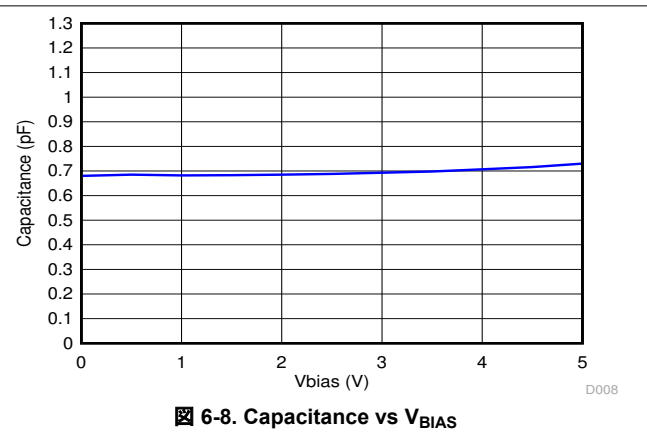
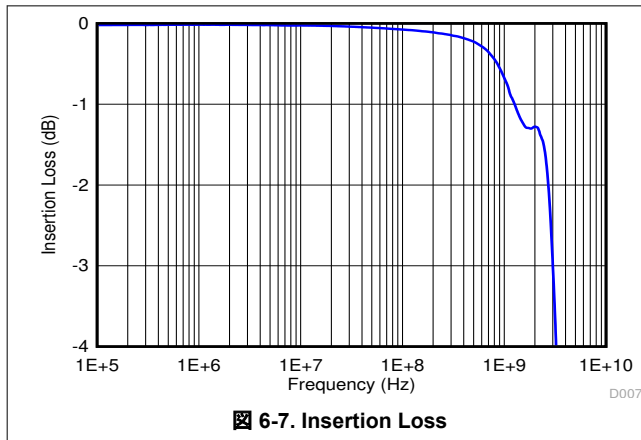


図 6-6. -8 kV IEC Waveform

## 6.6 Typical Characteristics (continued)

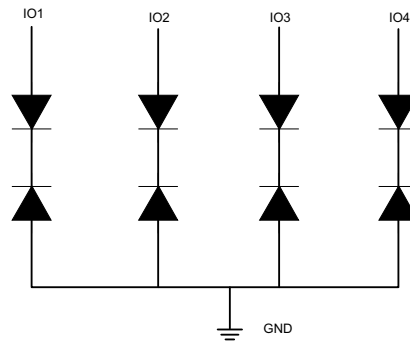


## 7 Detailed Description

### 7.1 Overview

The TPD4E1B06 is a 4-channel bi-directional Electrostatic Discharge (ESD) protection diode array. This device features ultra low leakage current (0.5 nA) for precision analog measurements. The  $\pm 12$  kV contact and  $\pm 15$  kV air gap ESD protection exceeds IEC 61000-4-2 level 4 requirements. The TPD4E1B06 0.7 pF line capacitance makes it suitable for precision analog, USB2.0, Ethernet, SATA, LVDS, and 1394 interfaces.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

TPD4E1B06 diode array structure uses back-to-back diode topology to accommodate bi-directional signaling between  $-5.5$  V and  $5.5$  V. Each pin has an additional 2 steering diodes, including the ground pin. The Zener diodes are not meant to be forward biased, creating the need for having the steering diodes. If there is  $+8$  V on IO1 and 0V on IO2, the IO1 Zener diode will breakdown and forward bias one of the steering diodes on IO2. The current will then flow out of IO2.

#### 7.3.1 Ultra Low Leakage Current 0.5 nA (Maximum)

TPD4E1B06 ultra-low leakage current supports long battery life and allows for precision analog measurements.

#### 7.3.2 Transient Protection for 4 I/O Lines

The four I/O pins of TPD4E1B06 can withstand ESD events up to  $\pm 12$  kV contact and  $\pm 15$  kV air gap per IEC61000-4-2.

#### 7.3.3 I/O Capacitance 0.7 pF (Typical)

TPD4E1B06 I/O pins present an ultra-low 0.7 pF capacitance to the protected signal lines, making it suitable for a wide range of applications.

#### 7.3.4 Bi-Directional (ESD) Protection Diode Array

TPD4E1B06 diode array structure uses back to back diode topology to accommodate bi-directional signaling between  $-5.5$  V and  $5.5$  V.

#### 7.3.5 Low ESD Clamping Voltage

TPD4E1B06 clamps ESD events to a safe level to protect system components.

### 7.4 Device Functional Modes

TPD4E1B06 is a passive integrated circuit that activates whenever fast transient voltages above  $V_{BR}$  or below  $-V_{BR}$  are present on the circuit being protected. During ESD events, voltages as high as  $\pm 12$  kV can be directed to ground through the internal diode network. Once the voltages on the protected line fall below the trigger levels of TPD4E1B06 (usually within 10's of nano-seconds) the device reverts to passive.



## 8 Application and Implementation

### 注

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### 8.1 Application Information

TPD4E1B06 is an ESD protection diode array which is typically used to provide a path to ground for dissipating ESD events on hi-speed signal lines between a human interface connector and a system. As the current from ESD passes through the diode, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low  $R_{DYN}$  of the triggered diode holds this voltage,  $V_{CLAMP}$ , to a safe level to the protected IC.

### 8.2 Typical Application

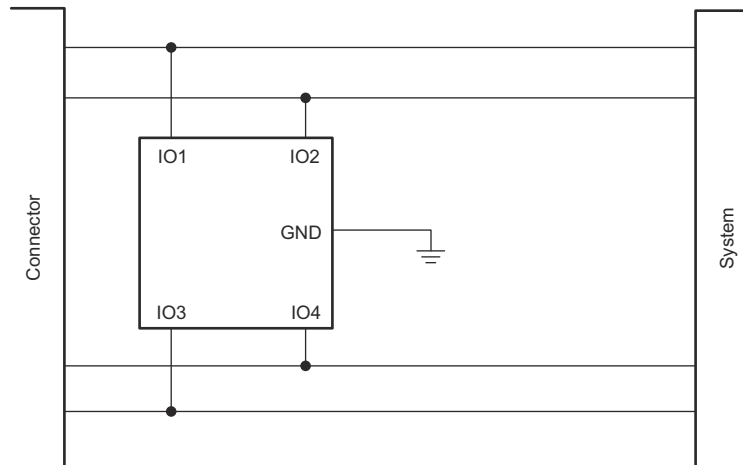


図 8-1. Protecting a Pair of Bi-Directional Differential Data Lines

The typical application of the TBD4E1B06 is to be placed in between the connector and the system. The low capacitance of the TBD4E1B06 gives flexibility in the end application, as it can be used on many different high speed interfaces.

#### 8.2.1 Design Requirements

表 8-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Signal range on IO1, IO2, IO3, IO4 Pins	–5.5 V to 5.5 V
Operating frequency	1.7 GHz

#### 8.2.2 Detailed Design Procedure

The designer needs to know the following:

- Signal range on all the protected lines
- Operating frequency

##### 8.2.2.1 Signal Range on IO1, IO2, IO3, and IO4 Pins

TPD4E1B06 has 4 protection channels for signal lines. Any I/O will support a signal range of –5.5 V to 5.5 V.

### 8.2.2.2 Operating Frequency

The 0.7 pF capacitance of each I/O channel supports data rates up to 3.4 Gbps.

### 8.2.3 Application Curves

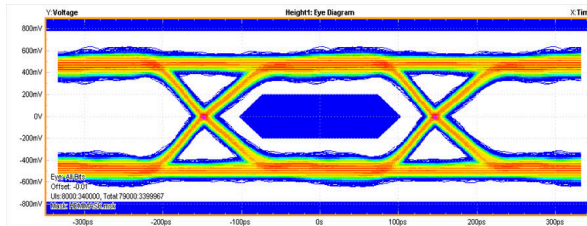


図 8-2. 3.4 Gbps HDMI 1.4 Eye Diagram in DCK Package

## 8.3 Layout

### 8.3.1 Layout Guidelines

- Place the device as close to the connector as possible.
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer should minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the diode and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the diode and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.

### 8.3.2 Layout Examples

図 8-3 shows a layout example for the TPD4E1B06DCK. Pins 1 and 2 and 4 and 5 are routed differentially. Pin 3 is routed to the ground plane. Pin 6 does not have an internal connection in the device and does not need to be routed anywhere on the board. It is also acceptable to connect pin 6 to the ground plane.

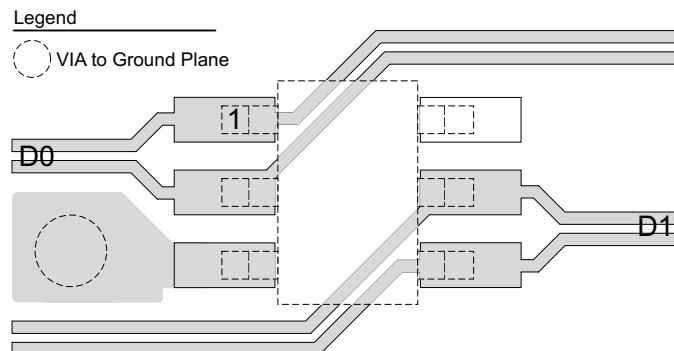


図 8-3. DCK Layout Example Showing Two Data Pairs, D0 and D1

図 8-4 shows a layout example for the TPD4E1B06DRL. Pins 1 and 6 and 3 and 4 are routed differentially. Pin 2 is routed to the ground plane. Pin 5 does not have an internal connection in the device and does not need to be routed anywhere on the board. It is also acceptable to connect pin 5 to the ground plane.

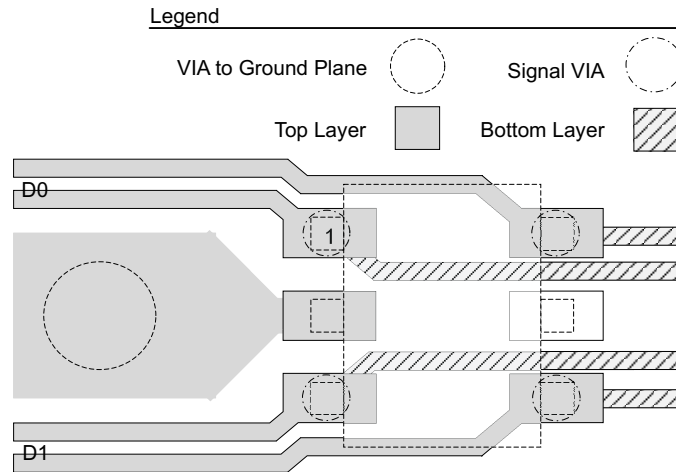


図 8-4. DRL Layout Example Showing Two Data Pairs, D0 and D1

## 9 Device and Documentation Support

### 9.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](https://www.ti.com) のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

### 9.2 サポート・リソース

**TI E2E™ サポート・フォーラム**は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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### 9.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

### 9.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

### 9.5 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPD4E1B06DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	BYP	<a href="#">Samples</a>
TPD4E1B06DRLR	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(BYG, BYH)	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD4E1B06DCKR	SC70	DCK	6	3000	178.0	8.4	2.4	2.5	1.2	4.0	8.0	Q3
TPD4E1B06DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
TPD4E1B06DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3

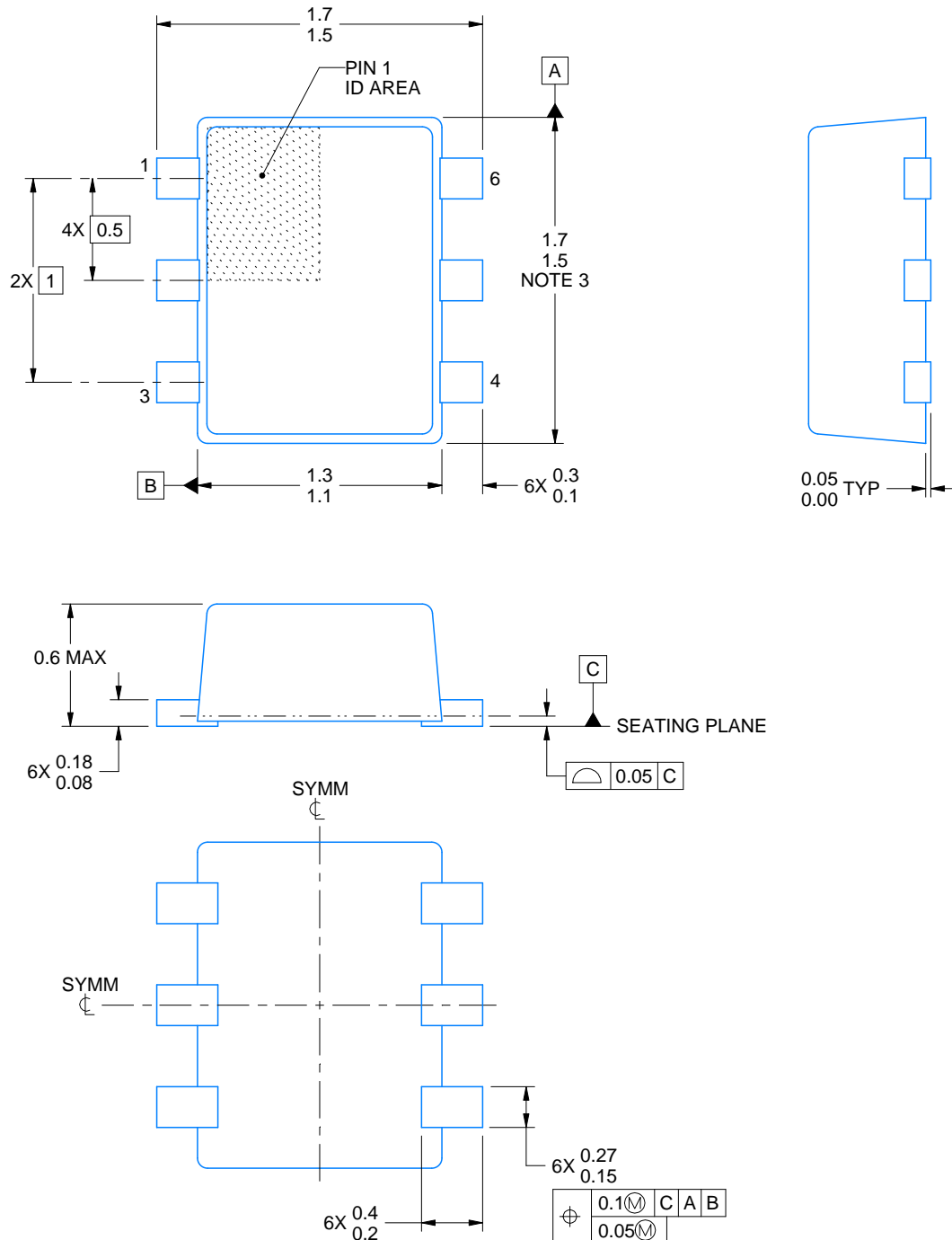
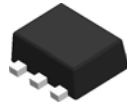
## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPD4E1B06DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
TPD4E1B06DRLR	SOT-5X3	DRL	6	4000	183.0	183.0	20.0
TPD4E1B06DRLR	SOT-5X3	DRL	6	4000	210.0	185.0	35.0





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## NOTES:

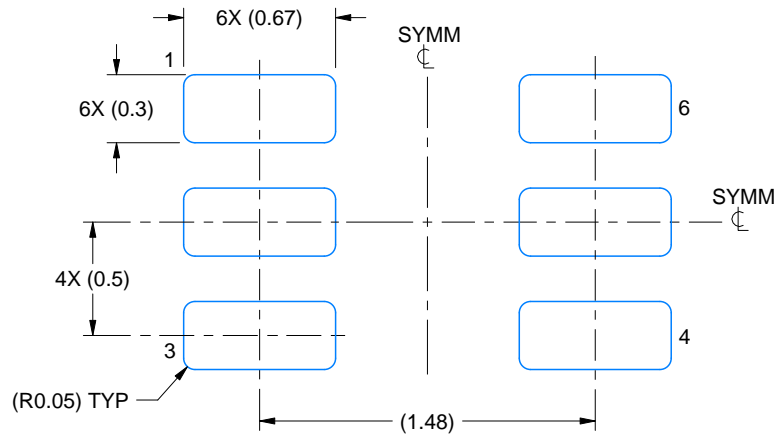
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-293 Variation UAAD

# EXAMPLE BOARD LAYOUT

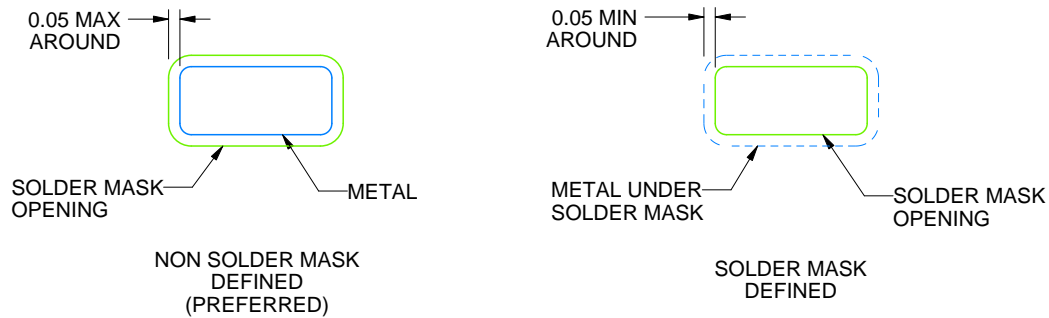
DRL0006A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE  
SCALE:30X



SOLDERMASK DETAILS

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NOTES: (continued)

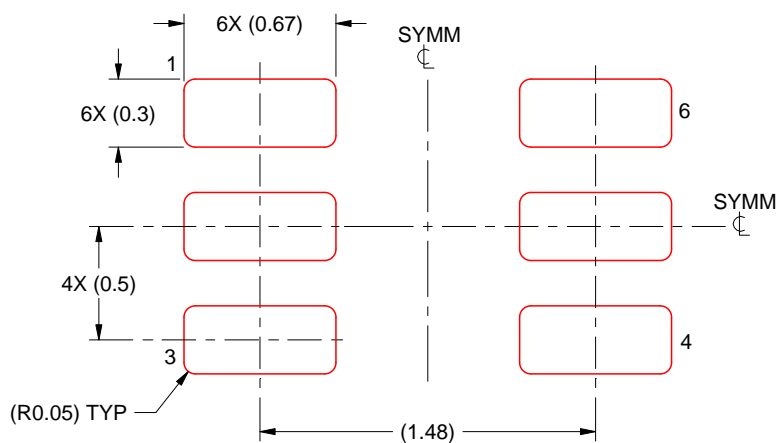
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.

## EXAMPLE STENCIL DESIGN

DRL0006A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE  
BASED ON 0.1 mm THICK STENCIL  
SCALE:30X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DCK (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



4093553-4/G 01/2007

NOTES:

- A. All linear dimensions are in millimeters.  
B. This drawing is subject to change without notice.  
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.  
D. Falls within JEDEC MO-203 variation AB.

DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
  - D. Publication IPC-7351 is recommended for alternate designs.
  - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

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